

**Pseudo SRAM**

<b>Part No.</b>	<b>W966D6HBG</b>	
<b>Datasheet</b>		
<b>Description</b>	This is a 64M bit CellularRAM™ compliant products, organized as 4M word by 16 bite; high-speed, CMOS pseudo-static random access memories developed for low-power, portable applications.	
<b>Features</b>	Supports asynchronous and burst operations VCC, VCCQ Voltages:1.7V–1.95V VCC, 1.7V–1.95V VCCQ Random access time: 70ns Burst mode READ and WRITE access: 4, 8, 16, or 32 words, or continuous burst Burst wrap or sequential Max clock rate: 133 MHz (tCLK = 7.5ns) tACLK: 5.5ns at 133 MHz, 7ns at 104 MHz Low-power features: TCR, PAR, DPD Page mode READ access:Sixteen-word page size Interpage READ access: 70ns, Intrapage READ access: 20ns	
<b>Diagram</b>	N/A	
<b>Package</b>	54VFBGA(6X8X1.0mm), RoHS compliant	
<b>Other Files</b>	<b>IBIS Model</b>	N/A
	<b>Spice Model</b>	N/A
	<b>Verilog Model</b>	N/A
<b>Development Tools</b>	N/A	
<b>Others</b>	N/A	

Contact us: [PSRAM@winbond.com](mailto:PSRAM@winbond.com)